

report4

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Target Specifications

- Output Voltage = $1.2\text{V} \pm 1\%$
- Supply Voltage = $1.8\text{V} \pm 10\%$
- Power Consumption $< 500\mu\text{W}$
- Temperature Range: -40°C to 125°C

Bias Currents

$$(I_{\text{total}})_{\text{max}} = \frac{500\mu\text{W}}{1.8\text{V}} = 277.8\mu\text{A}$$

Current Division

$$85\mu\text{A} + 85\mu\text{A} + 85\mu\text{A} + 20\mu\text{A} \quad (\text{approx. } 10\%)$$

Design Equations

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$$\begin{aligned} \frac{\frac{k}{q} \ln(n)}{R_1} &= \frac{0.002}{R_2} \\ \Rightarrow \frac{R_2}{R_1} &\approx 11.18 \end{aligned} \tag{1}$$

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$$85\mu = \frac{\frac{k}{q}(233) \ln n + V_{\text{OS}}}{R_1} + \frac{0.6}{R_2} \tag{2}$$

Solving:

$$R_1 = 1239.76 \Omega, \quad R_2 \approx 14,000 \Omega$$

Current Mirrors

$$\begin{aligned} R_3 &= \frac{1.2}{85\mu\text{A}} \\ &= 14,117.6 \Omega \end{aligned}$$

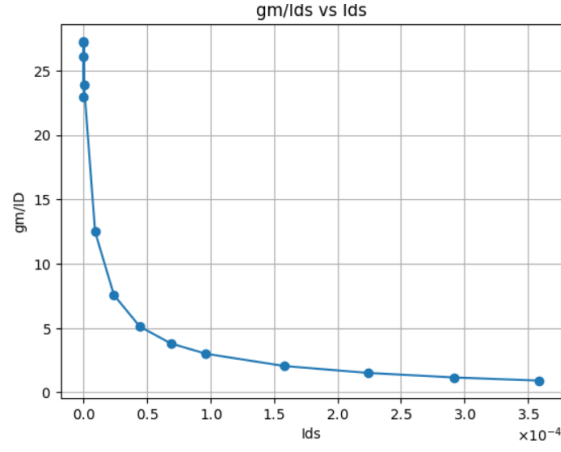


Figure 1: NMOS characteristics

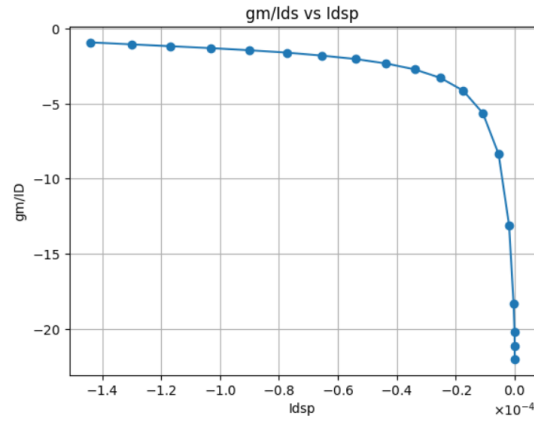


Figure 2: PMOS characteristics

- The PMOS for Output Voltage has the lowest headroom available.

$$[1.8 - 10\%] - [1.2 + 1\%]$$

$$\frac{g_m}{I_D} = \frac{2}{V_{DSAT}} = \frac{2}{400 \text{ mV}} = 5$$

$$I_{\text{per unit width}} \approx 15 \mu A$$

- Due to CLM, current is lower here than other branches.

$$m = \frac{85}{15} = 5.666 \Rightarrow \text{Round off to 5 (lower)}$$

Observations

$$R_1 = 2,200 \Omega$$

$$R_2 = 15,000 \Omega$$

Currents

$$74 \mu A, \quad 80 \mu A, \quad 80 \mu A, \quad 30 \mu A \quad (11.4\%)$$

$$R_3 = \frac{1.2}{74 \mu A}$$

$$= 16.2k \Omega$$

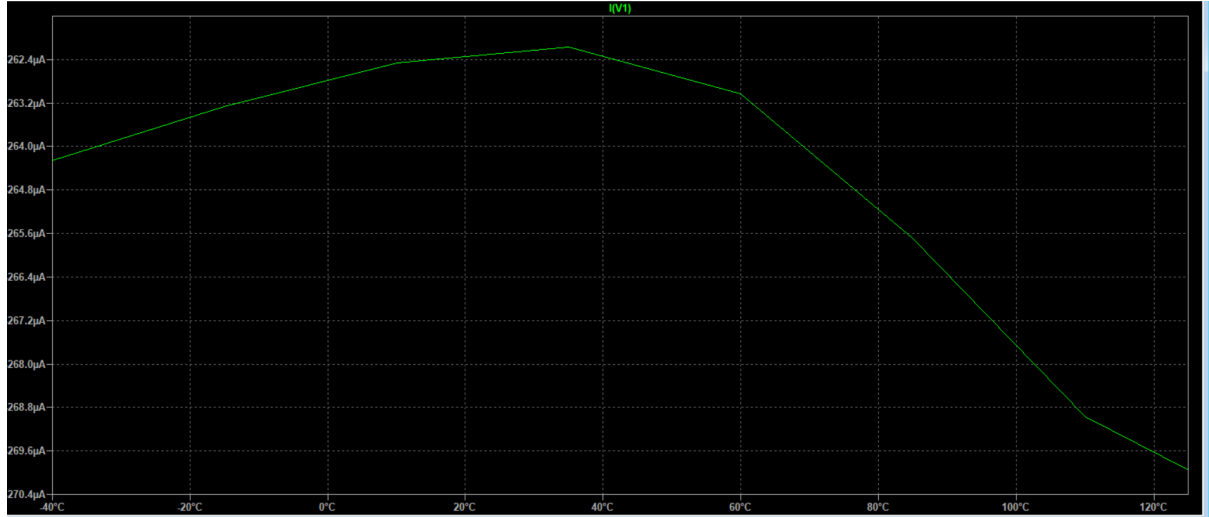


Figure 3: Total Current consumed

Bandgap Reference :

- Voltage Output at 27 degrees: 1.1947398V.
- Range of errors : +9 to -12 mV (within 1 percent of 1.2 volt).
- Maximum power : $486.72 \mu W$.

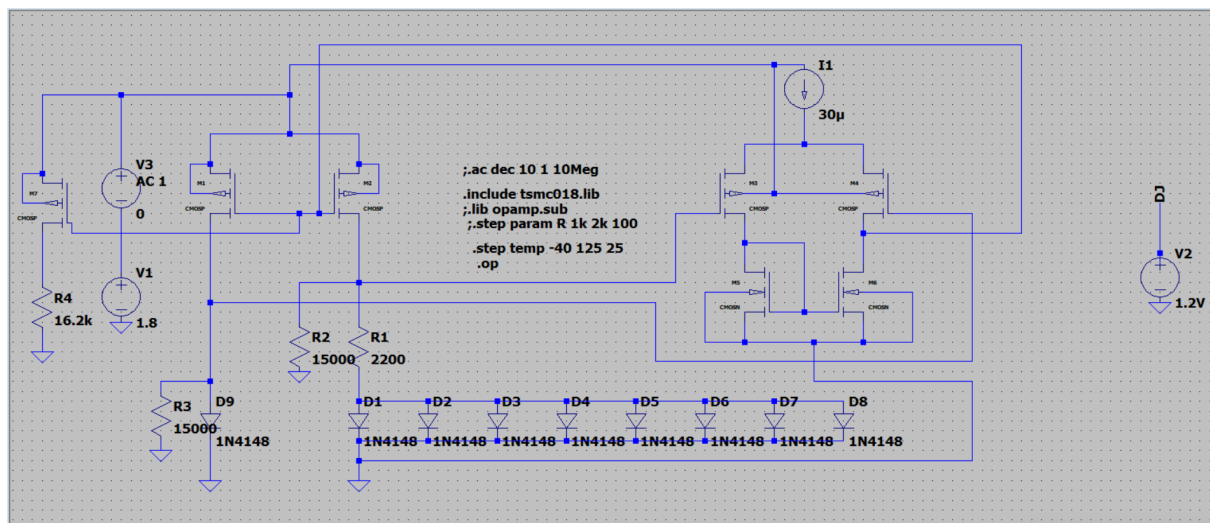


Figure 4:

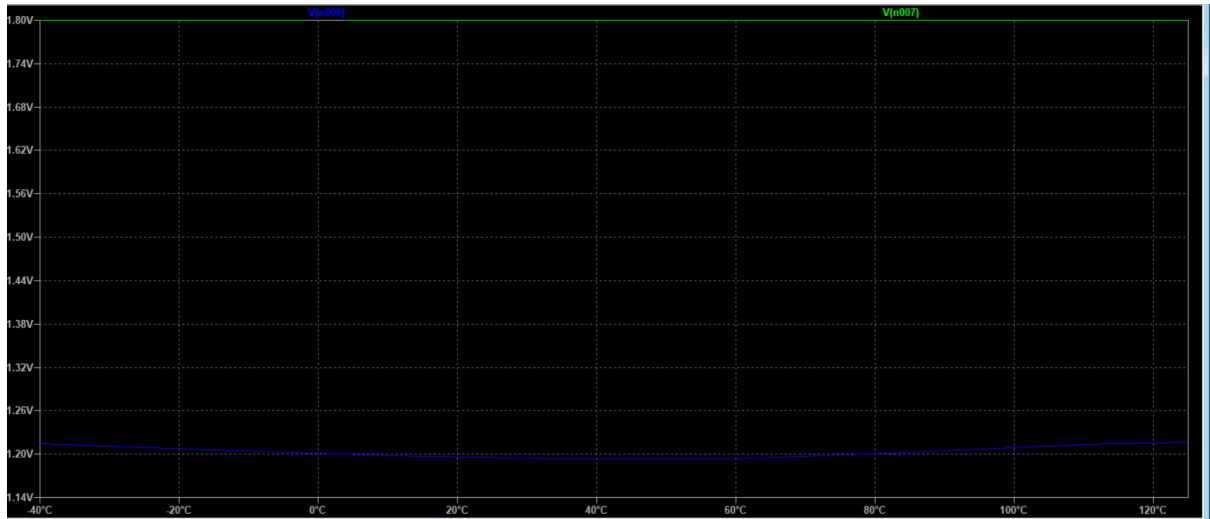


Figure 5: Output voltage

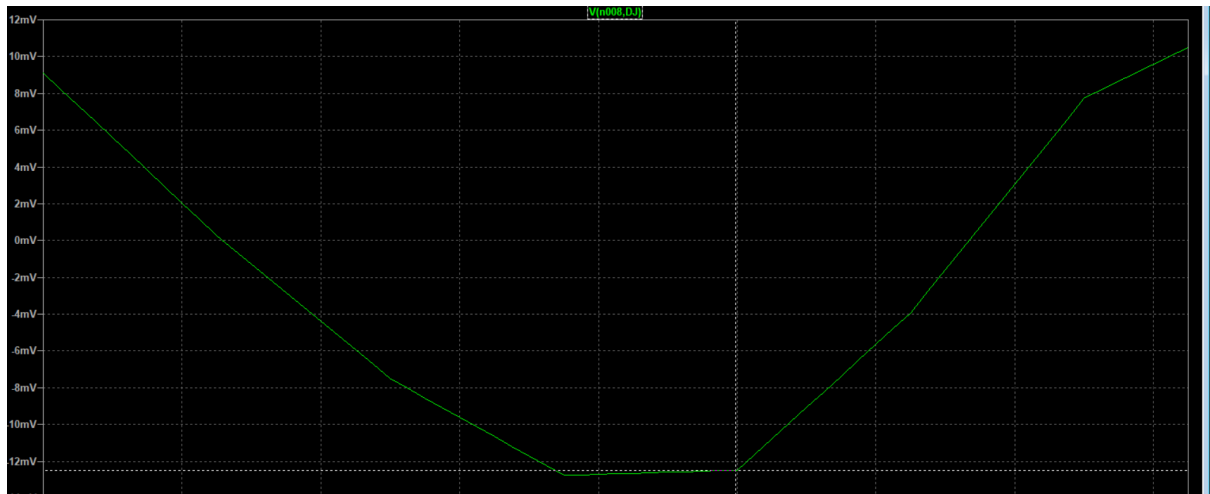


Figure 6: errors in output voltage

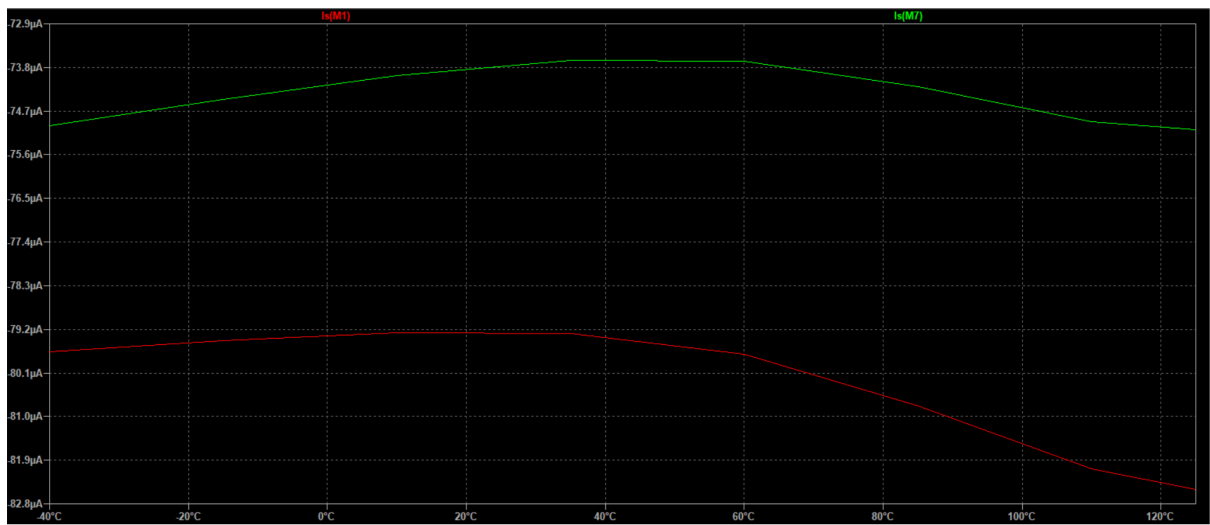


Figure 7: Current values